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**AMENDMENT**

(Amendment based upon the provision of Article 11 of said Law)

To: Examiner of the Patent Office

1. Identification of the International Application  
PCT/JP2004/004072

2. Applicant

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4. Item to be amended: Claims

5. Subject Matter of Amendment

The applicant has amended claim 1, and claims 2 to 4 are unchanged. The whole wording of claim 1 has been rewritten in order to make the feature of claim 1 clear. Support for change to "a non-doped layer stacked on the silicon substrate, the non-doped layer having an amorphous silicon phase and a microcrystalline silicon phase mixed together" can be found at page 9, line 25 to page 10, line 1 of the specification.

6. List of Attached Documents

(1) Replacement sheet of page 49

## CLAIMS

1. (Amended) A solar cell comprising:  
a silicon substrate for a solar cell, the  
substrate comprising a base composed of a  
5 polycrystalline metal-grade silicon solidified in one  
direction and a high-purity polycrystalline silicon  
layer stacked on a surface of the base; and  
a non-doped layer stacked on the silicon  
substrate, the non-doped layer having an amorphous  
10 silicon phase and a microcrystalline silicon phase  
mixed together.
2. (Unchanged) A solar cell according to claim  
1, wherein a thickness of the layer having the non-  
doped amorphous silicon phase and the  
15 microcrystalline silicon phase mixed together ranges  
from 1 nm to 15 nm.
3. (Unchanged) A solar cell according to claim  
1 or 2, wherein a ratio of the amorphous silicon  
phase and the microcrystalline silicon phase in the  
20 layer having the non-doped amorphous silicon phase  
and the microcrystalline silicon phase mixed together  
ranges from 1:1 to 10:1.
4. (Unchanged) A solar cell comprising a  
crystalline silicon substrate or a crystalline  
25 silicon layer, a layer having an amorphous silicon  
phase and a microcrystalline silicon phase mixed  
together, and a polycrystalline silicon layer grown  
with the microcrystalline silicon phase as a seed,  
which are stacked in mentioned order.